

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	2	(substrate or wafer or semiconductor) and chamber and (propylene or propyne or propane or butane or butylene or butadiene or acetelyne) and argon and plasma and ("RF" or "radio frequency") and (amorphous near4 carbon) and (hydrogen or oxygen) and etch\$4 and resist and ("silicon nitride" or "silicon carbide" or "carbon-doped silicon oxide" or "amorphous carbon") and dielectric and "dual frequency" and ("ARC" or "anti reflective coating")	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/12/16 08:41
L3	1	10/799146	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/12/16 10:52

S1	107	((("6635583B2") or ("6624064B1") or ("6573030") or ("6541397B1") or ("6458516B1") or ("6423384B1") or ("6413852") or ("6380106") or ("6358573B1") or ("6333255") or ("6331380B1") or ("6323119B1") or ("6316347") or ("6291334B1") or ("6235629") or ("6214730") or ("6211065B1") or ("6165890") or ("6153935") or ("6143476") or ("6140226") or ("6140224") or ("6098568") or ("6080529") or ("6066577") or ("6064118") or ("6057226") or ("6035803") or ("6030901") or ("6008140") or ("5986344") or ("5900288") or ("5866920") or ("5789320") or ("5759913") or ("5461003") or ("6852647") or ("6624064") or ("6596627") or ("6541842") or ("6428894") or ("6358804") or ("6346747") or ("6214637") or ("6203898") or ("6184572") or ("6183930") or ("6054379") or ("5930655") or ("5981000") or ("5882830") or ("5830332") or ("5262262") or ("5022959") or ("5674573") or ("5998100") or ("6352922") or ("6653735") or ("DE10328578") or ("EP381109") or ("EP901156") or ("JP9045633") or ("JP11026578") or ("4975144") or ("6043167") or ("6428894") or ("6884733")).PN. or ((2003/0091938A1) or (2002/0090794A1) or (2002/0086547A1) or (2002/0001778A1) or (2001/0007788A1) or (2004/0038537A1) or (2004/0023502) or (2004/0166691A1) or (2004/0180551A1) or (2004/0038537) or (2004/0229470)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/14 08:15
S2	7	S1 and (substrate or wafer or semiconductor) and chamber and (propylene or propyne or propane or butane or butylene or butadiene or acetelyne) and argon and plasma and ("RF" or "radio frequency") and (amorphous near4 carbon)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/12/14 08:22

S3	6	S1 and (substrate or wafer or semiconductor) and chamber and (propylene or propyne or propane or butane or butylene or butadiene or acetelyne) and argon and plasma and ("RF" or "radio frequency") and (amorphous near4 carbon) and (hydrogen or oxygen)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/12/14 08:23
S4	1	S1 and (substrate or wafer or semiconductor) and chamber and (propylene or propyne or propane or butane or butylene or butadiene or acetelyne) and argon and plasma and ("RF" or "radio frequency") and (amorphous near4 carbon) and (hydrogen or oxygen) and etch\$4 and resist and ("silicon nitride" or "silicon carbide" or "carbon-doped silicon oxide" or "amorphous carbon") and dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/12/14 08:37
S5	6	(substrate or wafer or semiconductor) and chamber and (propylene or propyne or propane or butane or butylene or butadiene or acetelyne) and argon and plasma and ("RF" or "radio frequency") and (amorphous near4 carbon) and (hydrogen or oxygen) and etch\$4 and resist and ("silicon nitride" or "silicon carbide" or "carbon-doped silicon oxide" or "amorphous carbon") and dielectric and "dual frequency"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/12/16 10:52